

40V LOGIC LEVEL GATE DRIVE MOSFET



Features

- Split-gate trench (SGT) design enhances overall performance
- On-resistance of only 85mΩ reduces power losses
- A gate charge of 21nC facilitates fast, efficient switching
- Low conduction losses enable higher efficiency



Benefits

Delivers robust, reliable performance in operating junction temperatures up to 175°C.

Compact DFN5x6 package ideal for demanding industrial and consumer applications.

MCC's 40V Logic Level Gate Drive MOSFET

Boost Performance with



Applications





Battery Battery protection management systems (BMS)

Low Gate Charge Meets Low RDS(on) in DFN5060 Package





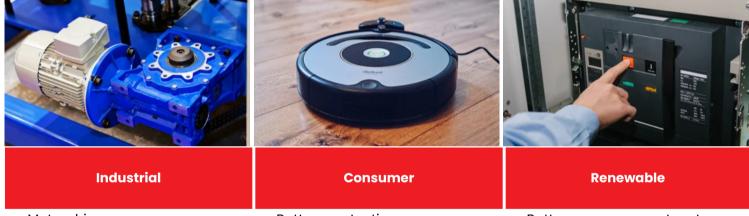
Accelerated Switching for Diverse Applications



Product Attributes, Parametrics & Datasheets

Product	Туре	Package	Drain- Source Voltage	Drain-Source On-Resistance RDS(on)(max)	Mounting Type	Datasheet
MCACLD85N04YL	N-Channel Power MOSFET	DFN5060	40V	85mΩ	Surface- Mount (SMD)	<u>Info</u>

Applications:



- Motor drives
- DC-DC converters

- Battery protection
- · Lighting controls

• Battery management systems (BMS)

CONTACT MCC TO REQUEST A SAMPLE